



**INTEGRATED CIRCUITS, SILICON MONOLITHIC, CMOS  
8-BIT ROMLESS MICROCONTROLLER**

**BASED ON TYPE 80C32E**

**ESCC Detail Specification No. 9521/002**

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DCR No.	CHANGE DESCRIPTION
936	Specification upissued to incorporate editorial changes per DCR.

**TABLE OF CONTENTS**

1	GENERAL	5
1.1	SCOPE	5
1.2	APPLICABLE DOCUMENTS	5
1.3	TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	5
1.4	THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS	5
1.4.1	The ESCC Component Number	5
1.4.2	Component Type Variants	5
1.5	MAXIMUM RATINGS	6
1.6	HANDLING PRECAUTIONS	6
1.7	PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION	7
1.7.1	Ceramic Multilayer Dual-in-Line Package (MDIL40) - 40 Pin	7
1.7.2	Ceramic Multilayer J-BEND Leaded Chip Carrier (MQFPJ44) - 44 Lead	8
1.7.3	Notes to Physical Dimensions and Terminal Identification	9
1.8	FUNCTIONAL DIAGRAM	10
1.9	PIN ASSIGNMENT	10
1.10	TIMING DIAGRAMS	14
1.11	INPUT PROTECTION NETWORKS	17
2	REQUIREMENTS	18
2.1	GENERAL	18
2.1.1	Deviations from the Generic Specification	18
2.1.1.1	Deviations from Screening Tests - Chart F3	18
2.2	MARKING	18
2.3	ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES	18
2.3.1	Room Temperature Electrical Measurements	18
2.3.2	High and Low Temperatures Electrical Measurements	25
2.4	PARAMETER DRIFT VALUES	26
2.5	INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS	26
2.6	POWER BURN-IN CONDITIONS	28
2.7	OPERATING LIFE CONDITIONS	28
2.8	TOTAL DOSE RADIATION TESTING	29
2.8.1	Bias Conditions and Total Dose Level for Total Dose Radiation Testing	29
2.8.2	Electrical Measurements for Total Dose Radiation Testing	29

## 1 GENERAL

### 1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

### 1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 9000
- (b) MIL-STD-883, Test Methods and Procedures for Microelectronics

### 1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

### 1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

#### 1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 952100201P

- Detail Specification Reference: 9521002
- Component Type Variant Number: 01 (as required)
- Total Dose Radiation Level Letter: P (as required)

#### 1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and Finish	Weight max g	Total Dose Radiation Level Letter
01	80C32	MDIL40	D2	8	P [30kRAD(Si)]
02	80C32	MQFPJ44	G3	5	P [30kRAD(Si)]

The lead/terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

The total dose radiation level letter shall be as defined in ESCC Basic Specification no. 22900. If an alternative radiation test level is specified in the Purchase Order the letter shall be changed accordingly.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Supply Voltage	$V_{DD}$	-0.3 to 7	V	Note 1
Input Voltage Range	$V_{IN}$	-0.3 to $V_{DD}+0.3$	V	Notes 1, 2
Output Current	$I_{OUT}$	$\pm 80$	mA	Note 3
Device Power Dissipation (Continuous)	$P_D$	1	W	
Operating Temperature Range	$T_{op}$	-55 to +125	$^{\circ}C$	$T_{amb}$
Storage Temperature Range	$T_{stg}$	-65 to +150	$^{\circ}C$	
Soldering Temperature	$T_{sol}$	+265	$^{\circ}C$	Note 4
Junction Temperature	$T_j$	+165	$^{\circ}C$	
Thermal Resistance, Junction to Case For MDIL40 For MQFPJ44	$R_{th(j-c)}$	8 6	$^{\circ}C/W$	

**NOTES:**

1. All voltages are with respect to  $V_{SS}$ . Device is functional for  $4.5V \leq V_{DD} \leq 5.5V$ .
2.  $V_{DD}+0.3V$  shall not exceed 7V.
3. The maximum output current of any single output.
4. Duration 10 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 HANDLING PRECAUTIONS

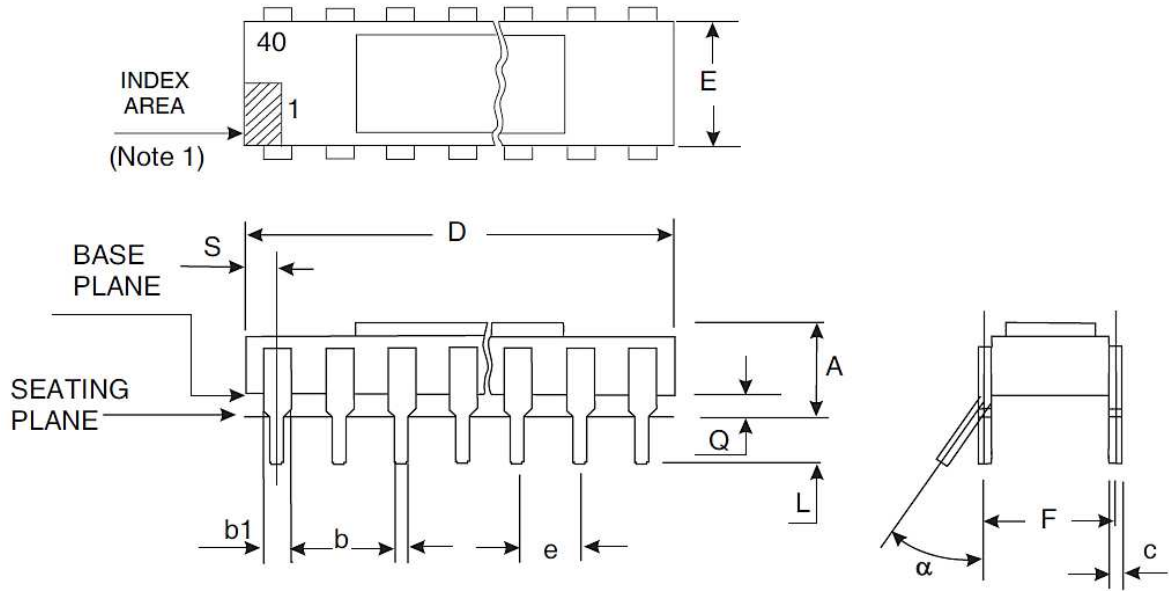
These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 1 per ESCC Basic Specification No. 23800 with a Minimum Critical Path Failure Voltage of 500 Volts.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

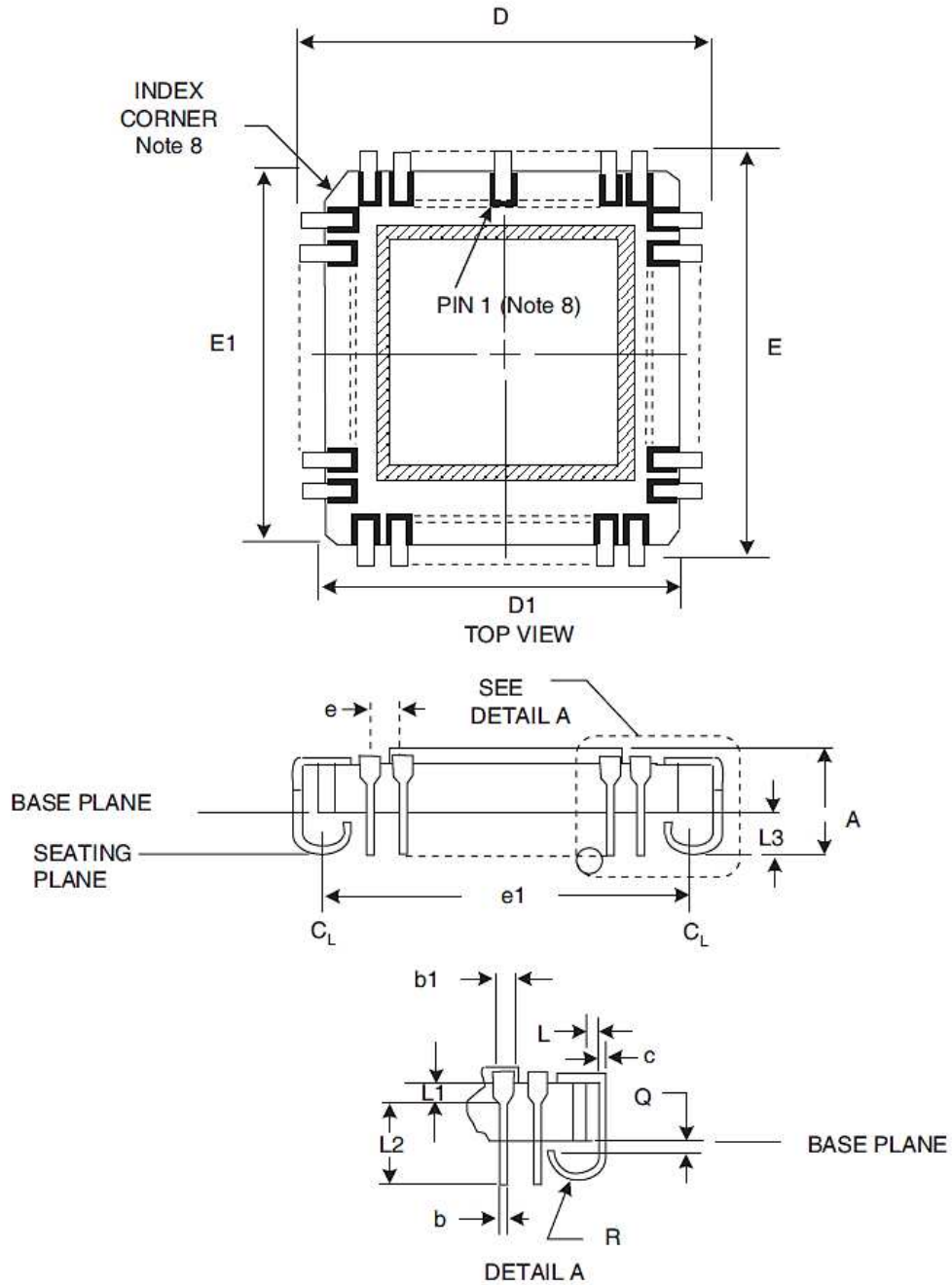
Consolidated Notes are given following the case drawings and dimensions.

1.7.1 Ceramic Multilayer Dual-in-Line Package (MDIL40) - 40 Pin



Symbols	Dimensions mm		Notes
	Min	Max	
A	2.16	4.83	2
b	0.38	0.58	3
b1	0.97	1.52	3
c	0.2	0.3	3
D	50.3	51.56	
E	14.74	15.49	
e	2.54 BSC		3, 4
F	15.12	15.87	3, 5
L	3.18	4.44	2, 3
S	0.77	1.65	6
Q	0.51	1.77	2, 7
alpha	0°	15°	3

1.7.2 Ceramic Multilayer J-BEND Leaded Chip Carrier (MQFPJ44) - 44 Lead



Symbols	Dimensions mm		Notes
	Min	Max	
A	2.67	4.95	
b	0.33	0.56	9
b1	0.55	0.88	9
c	0.17	0.25	9

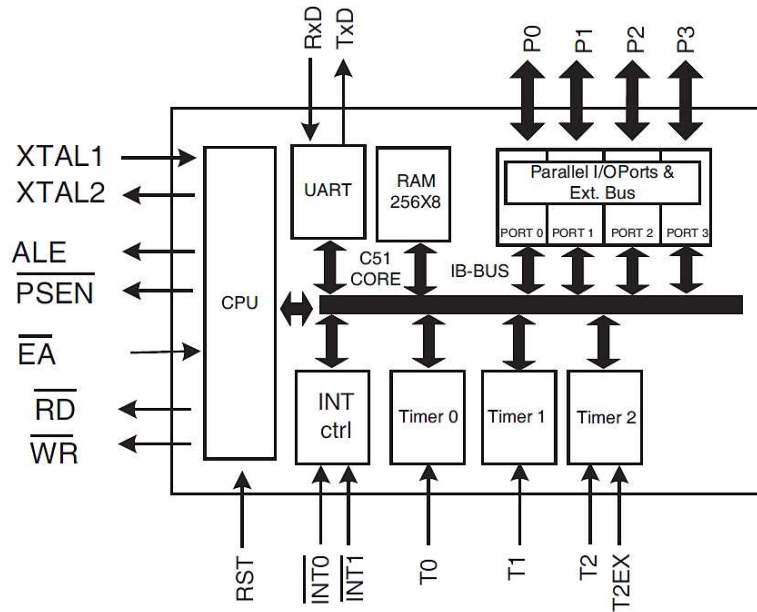


Symbols	Dimensions mm		Notes
	Min	Max	
D/E	17.14	17.78	
D1/E1	15.74	16.76	
e	1.27 BSC		9, 10
e1	16 BSC		11
L	0.12	-	9
L1	0.51	-	9
L2	0.63	-	9
L3	0.58	-	9, 12
Q	0.07	-	
R	0.5	1.01	9

1.7.3 Notes to Physical Dimensions and Terminal Identification

1. Index area; a notch or a dot shall be located adjacent to Pin 1 and shall be within the shaded area shown.
2. Dimensions are measured with the package seated in a seating plane gauge.
3. All leads.
4. 38 places. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within  $\pm 0.25$ mm of its true longitudinal position relative to Pin 1 and the highest pin number.
5. Dimensions are measured with the leads constrained to be perpendicular to the base plane.
6. Two places.
7. The dimension shall be measured from the seating plane to the base plane.
8. A terminal identification mark shall be located in the region of Pin 1 as shown. Terminal numbers shall increase counter-clockwise when viewed as shown starting from the centre terminal (Pin 1). The index corner shall be clearly unique but may vary from that shown on the drawing.
9. Applies to all 44 terminations (11 per side).
10. 40 places. The true position pin spacing is 1.27mm between centrelines. Each pin centreline shall be located within  $\pm 0.25$ mm of its true longitudinal position relative to the package centrelines.
11. Four places.
12. Measured from Seating Plane to Base Plane (i.e., including dimension Q).

1.8 FUNCTIONAL DIAGRAM



1.9 PIN ASSIGNMENT

Pin	Name		Pin	Name	
	MDIL40	MQFPJ44		MDIL40	MQFPJ44
1	T2/P1.0	-	23	P2.2	-
2	T2EX/P1.1	T2/P1.0	24	P2.3	P2.0
3	P1.2	T2EX/P1.1	25	P2.4	P2.1
4	P1.3	P1.2	26	P2.5	P2.2
5	P1.4	P1.3	27	P2.6	P2.3
6	P1.5	P1.4	28	P2.7	P2.4
7	P1.6	P1.5	29	$\overline{\text{PSEN}}$	P2.5
8	P1.7	P1.6	30	ALE	P2.6
9	RST	P1.7	31	$\overline{\text{EA}}$	P2.7
10	P3.0/RXD	RST	32	P0.7	$\overline{\text{PSEN}}$
11	P3.1/TXD	P3.0/RXD	33	P0.6	ALE
12	P3.2/ $\overline{\text{INT0}}$	-	34	P0.5	-
13	P3.3/ $\overline{\text{INT1}}$	P3.1/TXD	35	P0.4	$\overline{\text{EA}}$
14	P3.4/T0	P3.2/ $\overline{\text{INT0}}$	36	P0.3	P0.7
15	P3.5/T1	P3.3/ $\overline{\text{INT1}}$	37	P0.2	P0.6
16	P3.6/ $\overline{\text{WR}}$	P3.4/T0	38	P0.1	P0.5
17	P3.7/ $\overline{\text{RD}}$	P3.5/T1	39	P0.0	P0.4

Pin	Name		Pin	Name	
	MDIL40	MQFPJ44		MDIL40	MQFPJ44
18	XTAL2	P3.6/ $\overline{WR}$	40	V <sub>DD</sub>	P0.3
19	XTAL1	P3.7/ $\overline{RD}$	41	-	P0.2
20	V <sub>SS</sub>	XTAL2	42	-	P0.1
21	P2.0	XTAL1	43	-	P0.0
22	P2.1	V <sub>SS</sub>	44	-	V <sub>DD</sub>

Pin Name	Type Note 1	Function
Port 0 (P0.0-7)	I/O	Port 0 is an 8-bit open drain bi-directional I/O port. Port 0 pins that have 1's written to them float and, in that state, can be used as high impedance inputs. Port 0 is also the multiplexed low order address and data bus (A0 - A7) during access to external programme and data memory. In this application, it uses strong internal pull-ups when emitting 1's. External pull-ups are required during programme verification. Port 0 can sink eight LS TTL inputs.
Port 1 (P1.0-7)	I/O	Port 1 is an 8-bit bi-directional I/O port with internal pull-ups. Port 1 pins that have 1's written to them are pulled high by the internal pull-ups, and in that state can be used as inputs. As inputs, Port 1 pins that are externally being pulled low will source current because of the internal pull-ups. Port 1 also receives the lower address byte during programme verification. It can drive CMOS inputs without external pull-ups. Also in this device Port 1 can sink/source three LS TTL inputs. Two inputs of Port 1 are also used for Timer/Counter 2: <ul style="list-style-type: none"> <li>• P1.0: (T2) External Clock Inputs.</li> <li>• P1.1: (T2EX) Trigger input to be reloaded or captured causing Timer/Counter 2 to interrupt.</li> </ul>

Pin Name	Type Note 1	Function
Port 2 (P2.0-9)	I/O	Port 2 is an 8-bit bi-directional I/O port with internal pull-ups. Port 2 pins that have 1's written to them are pulled high by the internal pull-ups, and in that state can be used as inputs. As inputs Port 2 pins that are externally being pulled low will source current because of the internal pull-ups. Port 2 emits the high-order address byte (A8 - A15) during fetches from external Programme Memory and during accesses to external Data Memory that use 16-bit addresses. In this application, it uses strong internal pull-ups when emitting 1's. During access to external Data Memory that use 8-bit addresses, Port 2 emits the contents of the P2 Special Function Register (SFR - P2). Port 2 can sink/source three LS TTL inputs. It can drive CMOS inputs with external pull-ups. Port 2 also receives the high-order address bit and control signals during programme verification.
Port 3 (P3.0-7)	I/O	Port 3 is an 8-bit bi-directional I/O port with internal pull-ups. Port 3 pins that have 1's written to them are pulled high by the internal pull-ups and in that state can be used as inputs. As inputs, Port 3 pins that are externally being pulled low will source current because of the pull-ups. It also serves the functions of various special features of the 8051 family as listed in Note 2. Port 3 can sink/source three LS TTL inputs. It can drive CMOS inputs without external pull-ups.
RST	I	Device Reset: A high level on this pin for two machine cycles while the oscillator is running resets the device. An internal pull-down resistor permits Power-On reset using only a capacitor connector to $V_{DD}$ . As soon as the reset is applied ( $V_{IN}$ ), Ports 1, 2 and 3 are tied to "1". this operation is achieved asynchronously even if the oscillator does not start up.
ALE	O	Address Latch Enable output for latching the low byte of the address during accesses to external memory. ALE is activated as though for this purpose at a constant rate of 1/6 of the oscillator frequency except during an external data memory access, at which time one ALE pulse is skipped. ALE can sink/source 8 LS TTL inputs. It can drive CMOS inputs without an external pull-up.

Pin Name	Type Note 1	Function
$\overline{\text{PSEN}}$	O	Programme Store Enable output is the read strobe to external Programme Memory. $\overline{\text{PSEN}}$ is activated twice each machine cycle during fetches from external Programme Memory (however when executing out of external programme memory, two activations of $\overline{\text{PSEN}}$ are skipped during each access to external Data Memory). $\overline{\text{PSEN}}$ is not activated during fetches from internal Programme Memory. $\overline{\text{PSEN}}$ can sink/source 8 LS TTL inputs. It can drive CMOS inputs without an external pull-up.
$\overline{\text{EA}}$	I	When $\overline{\text{EA}}$ is held high, the CPU executes out of internal Programme Memory (unless the Programme Counter exceeds 3FFFH). When $\overline{\text{EA}}$ is held low, the CPU executes only out of external Programme Memory. $\overline{\text{EA}}$ must not be floated.
XTAL1	I	Input to the inverting amplifier that forms the oscillator. Receives the external oscillator signal when an external oscillator is used.
XTAL2	O	Output of the inverting amplifier that forms the oscillator and input of the internal clock generator. This pin should be floated when an external oscillator is used.

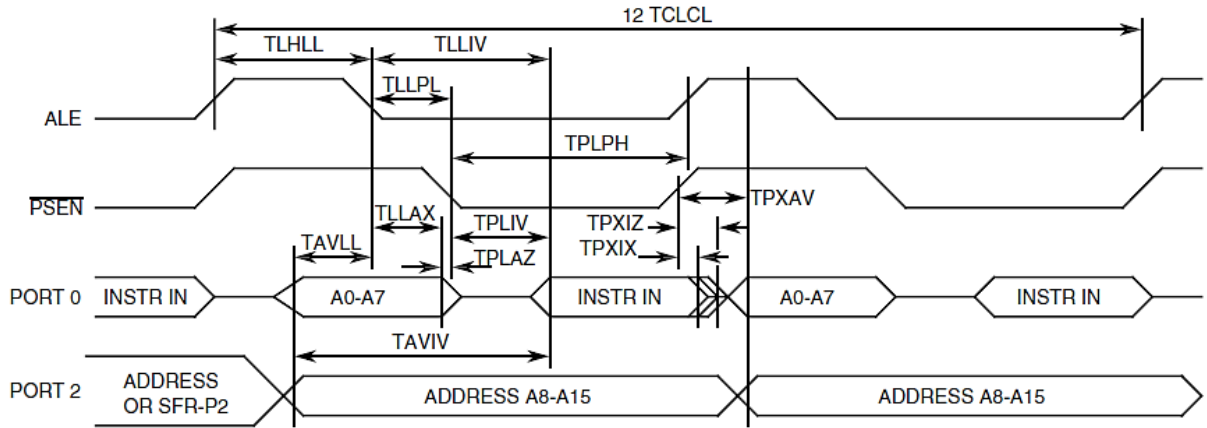
**NOTES:**

1. I = Input, O = Output, I/O = Input/Output.
2. Port 3 special features:

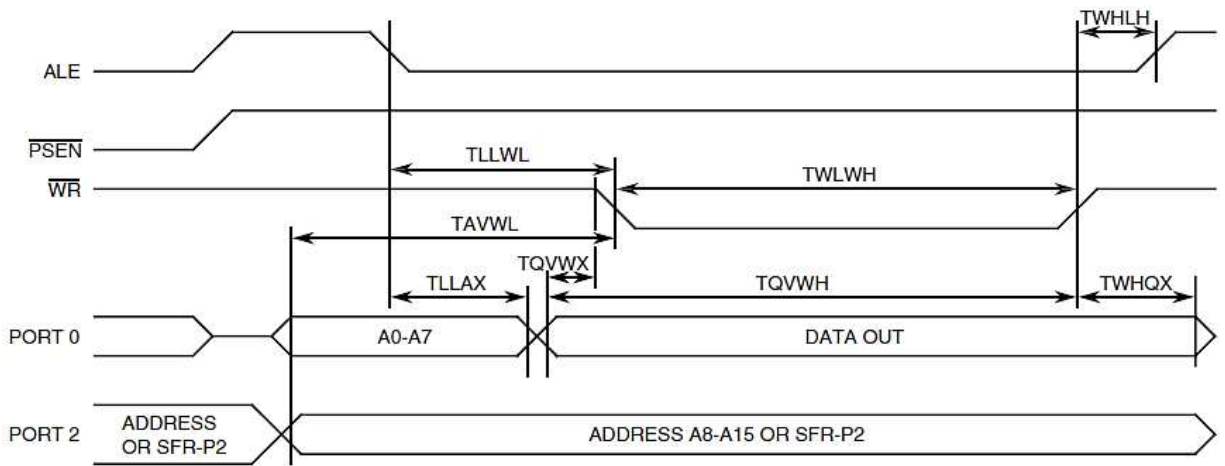
Port 3 Pin Name	Alternate Pin Name and Function
P3.0	RXD (Serial input port)
P3.1	TXD (Serial output port)
P3.2	$\overline{\text{INT0}}$ (External interrupt 0)
P3.3	$\overline{\text{INT1}}$ (External interrupt 1)
P3.4	T0 (Timer 0 external input)
P3.5	T1 (Timer 1 external input)
P3.6	$\overline{\text{WR}}$ (External data memory write strobe)
P3.7	$\overline{\text{RD}}$ (External data memory read strobe)

1.10 TIMING DIAGRAMS

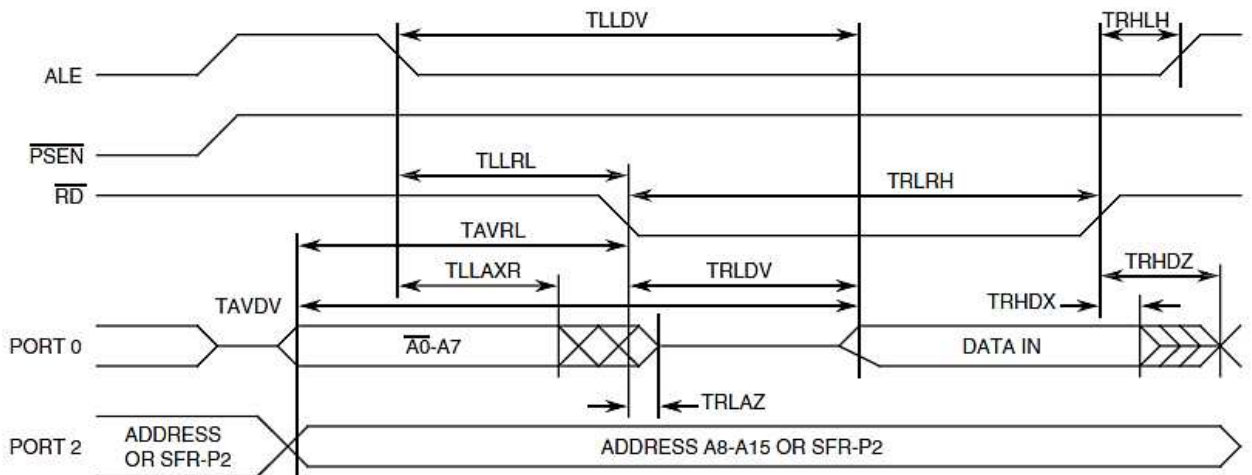
EXTERNAL PROGRAMME MEMORY READ CYCLE



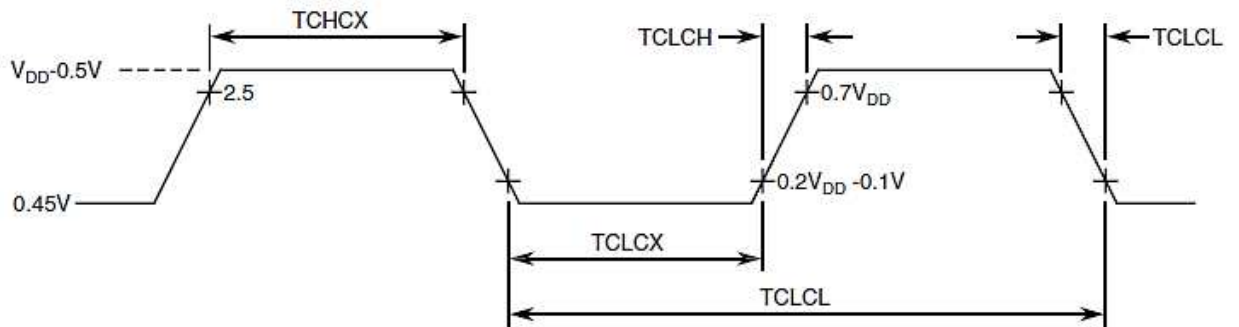
EXTERNAL DATA MEMORY WRITE CYCLE



EXTERNAL DATA MEMORY READ CYCLE



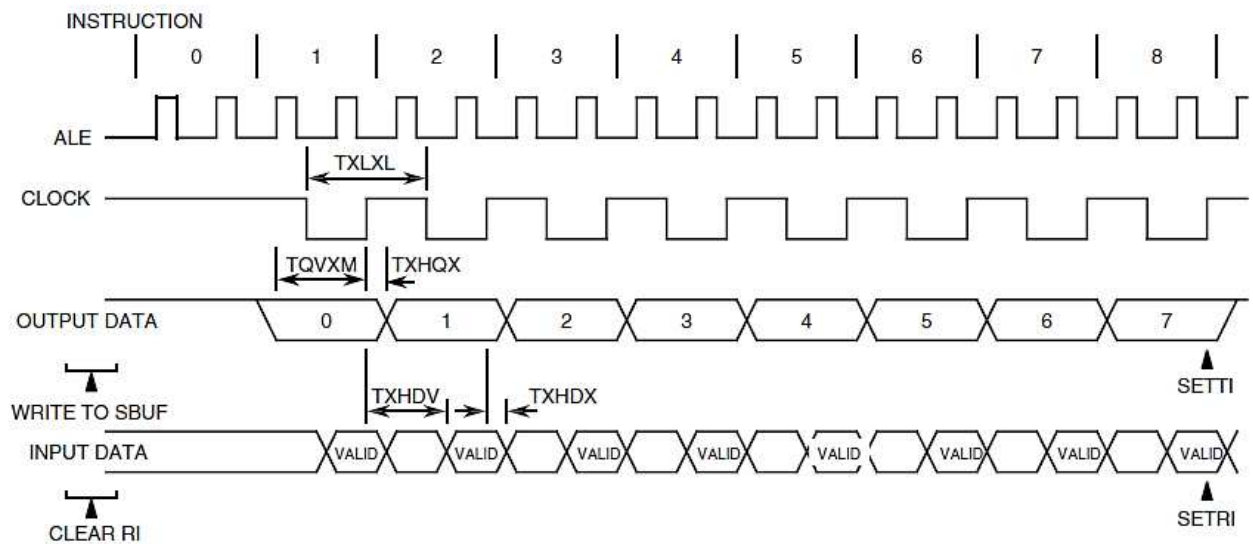
EXTERNAL CLOCK WAVEFORMS



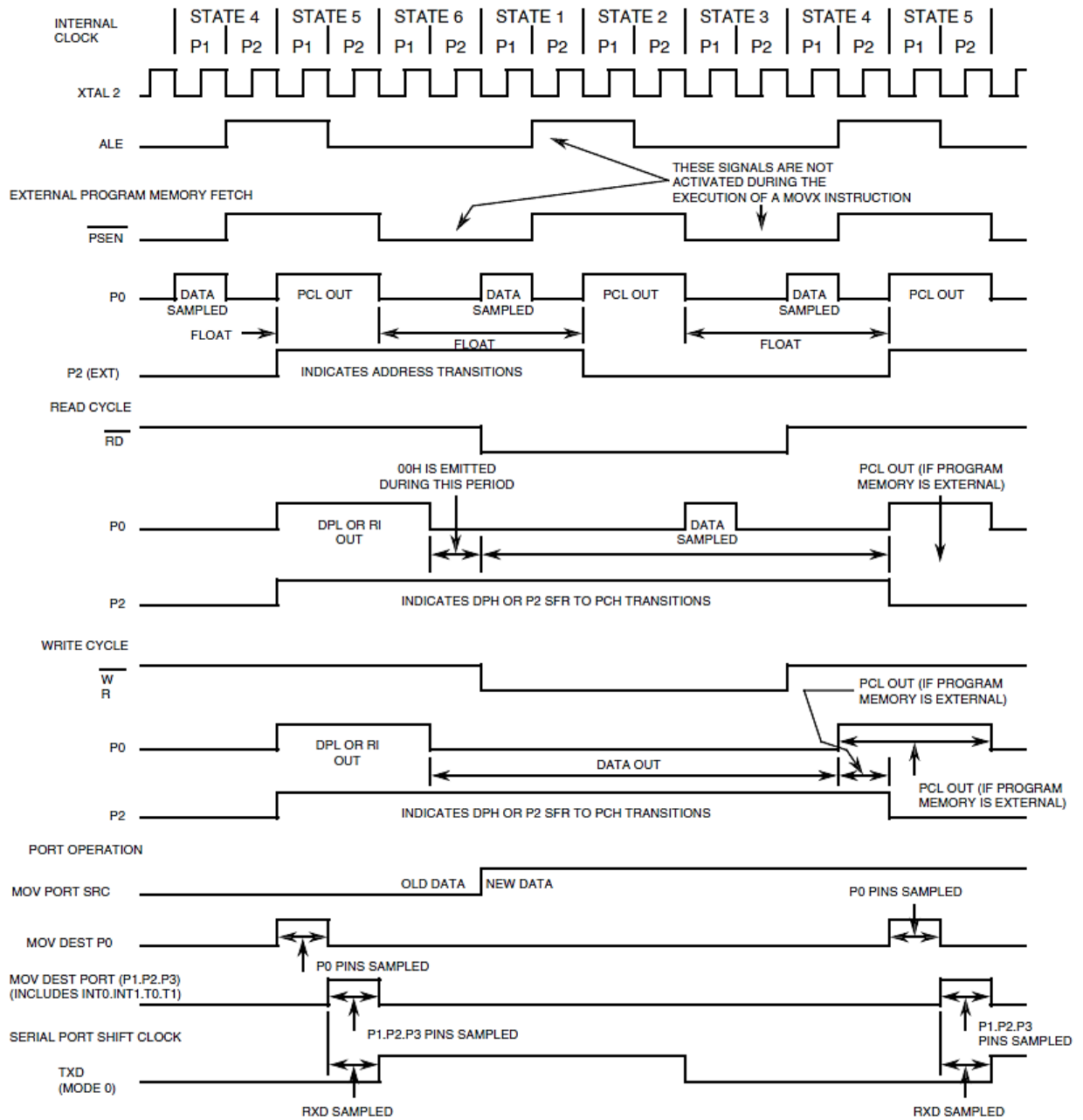
EXTERNAL CLOCK DRIVE CHARACTERISTICS (XTAL1)

Symbol	Parameter	Min.	Max.	Unit
TCLCL	Oscillator Period	33.33	-	ns
TCHCX	High Time	5	-	ns
TCLCX	Low Time	5	-	ns
TCLCH	Rise Time	-	5	ns
TCHCL	Fall Time	-	5	ns

SHIFT REGISTER TIMING WAVEFORMS



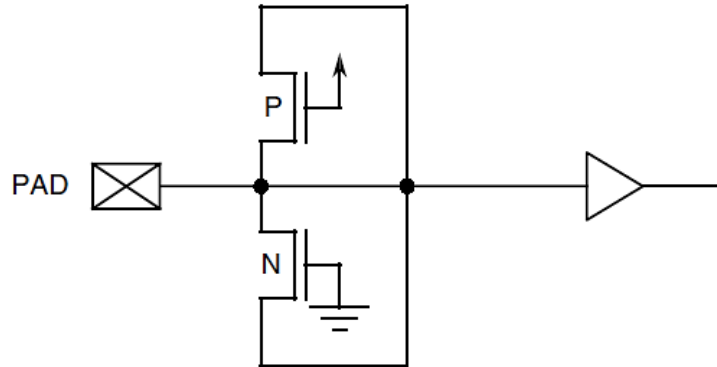
INTERNAL CLOCK WAVEFORMS



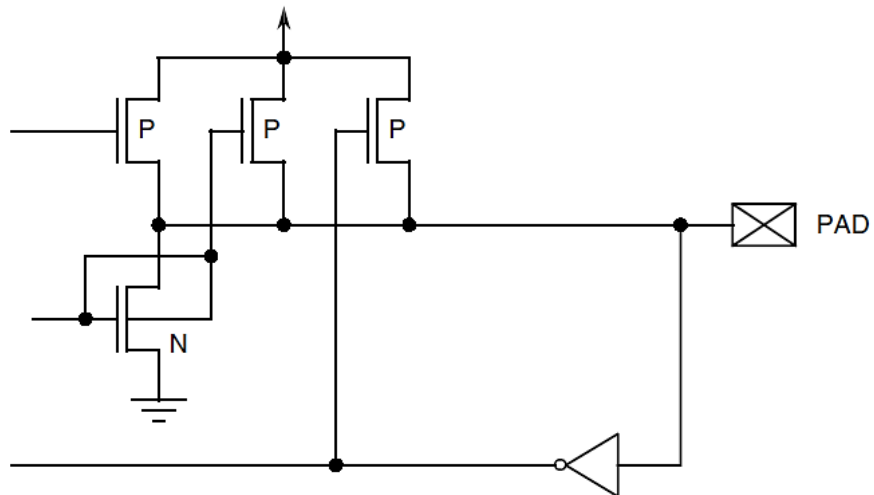


1.11 INPUT PROTECTION NETWORKS

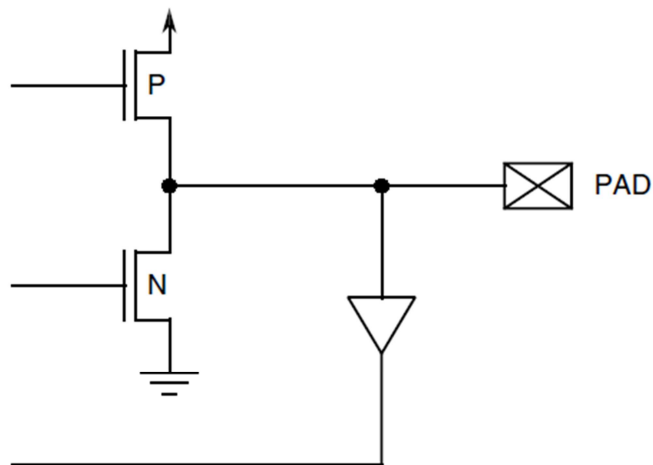
INPUTS  $\overline{EA}$ , RST, XTAL1



I/O'S P1.n, P2.n, P3.n



I/O'S P0.n, ALE,  $\overline{PSEN}$



**2 REQUIREMENTS**

**2.1 GENERAL**

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

**2.1.1 Deviations from the Generic Specification**

**2.1.1.1 *Deviations from Screening Tests - Chart F3***

High Temperature Reverse Bias Burn-in shall not be performed.

**2.2 MARKING**

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification.
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number.
- (d) Traceability information.

**2.3 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES**

Electrical measurements shall be performed at room, high and low temperatures.

**2.3.1 Room Temperature Electrical Measurements**

The measurements shall be performed at  $T_{amb} = +22 \pm 3^{\circ}C$ .

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Functional Test 1	-	3014	Verify Function without Load $V_{IL} = 0V, V_{IH} = 3V$ $V_{OUT} = 1.5V$ $f = 1MHz$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 2	-	-	-

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Functional Test 2	-	3014	Verify Function without Load $V_{IL} = 0V, V_{IH} = 3V$ $V_{OUT} = 1.5V$ $f = 1MHz$ $V_{DD} = 5.5V, V_{SS} = 0V$ Note 2	-	-	-
Functional Test 3	-	3014	Verify Function without Load $V_{IL} = 0.8V, V_{IH} = 2.2V$ $V_{OUT} = 1.5V$ $f = 1MHz$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 2	-	-	-
Functional Test 4	-	3014	Verify Function without Load $V_{IL} = 0.8V, V_{IH} = 2.2V$ $V_{OUT} = 1.5V$ $f = 1MHz$ $V_{DD} = 5.5V, V_{SS} = 0V$ Note 2	-	-	-
Functional Test 5	-	3014	Verify Function with Load $V_{IL} = 0V, V_{IH} = 3V$ $V_{OUT} = 1.5V$ $f = 1MHz$ Outputs: 1TTL+50pF $V_{DD} = 4.5V, V_{SS} = 0V$ Note 2	-	-	-
Functional Test 6	-	3014	Verify Function with Load $V_{IL} = 0V, V_{IH} = 3V$ $V_{OUT} = 1.5V$ $f = 1MHz$ Outputs: 1TTL+50pF $V_{DD} = 5.5V, V_{SS} = 0V$ Note 2	-	-	-
Functional Test 7	-	3014	Verify Function with Load $V_{IL} = 0V, V_{IH} = 3V$ $V_{OUT} = 1.5V$ $f = 12MHz$ Outputs: 1TTL+50pF $V_{DD} = 4.5V, V_{SS} = 0V$ Note 2	-	-	-

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Functional Test 8	-	3014	Verify Function with Load $V_{IL} = 0V$ , $V_{IH} = 3V$ $V_{OUT} = 1.5V$ $f = 12MHz$ Outputs: 1TTL+50pF $V_{DD} = 5.5V$ , $V_{SS} = 0V$ Note 2	-	-	-
Input Clamp Voltage 1, to $V_{SS}$	$V_{IC1}$	3022	$I_{IN}$ (Under Test) = 100mA All Other Pins Open $V_{DD} = \text{Open}$ , $V_{SS} = 0V$ Note 3	200	-	mV
Input Clamp Voltage 2, to $V_{DD}$	$V_{IC2}$	3022	$I_{IN}$ (Under Test) = 100mA All Other Pins Open $V_{DD} = 0V$ , $V_{SS} = \text{Open}$ Note 3	-	-200	mV
Low Level Input Leakage Current 1	$I_{IL1}$	3009	$V_{IN}$ (Under Test) = 450mV $V_{DD} = 5.5V$ , $V_{SS} = 0V$	-	$\pm 10$	$\mu A$
Low Level Input Leakage Current 2	$I_{IL2}$	3009	I/O Ports P1, P2, P3: $V_{IN}$ (Under Test) = 450mV $V_{IN}$ (Remaining Inputs) = 0V $V_{DD} = 5.5V$ , $V_{SS} = 0V$	-	-75	$\mu A$
High Level Input Leakage Current	$I_{IH}$	3010	$V_{IN}$ (Under Test) = 5.5V $V_{DD} = 5.5V$ , $V_{SS} = 0V$	-	$\pm 10$	$\mu A$
High Level to Low Level Transition Current	$I_{IT}$	-	I/O Ports P1, P2, P3: $V_{IN}$ (Under Test) = 2V $V_{IN}$ (Remaining Inputs) = 0V $V_{DD} = 5.5V$ , $V_{SS} = 0V$	-	-750	$\mu A$
Low Level Output Voltage 1	$V_{OL1}$	3007	I/O Port PO, ALE, PSEN: $I_{OL} = 3.2mA$ $V_{DD} = 4.5V$ , $V_{SS} = 0V$	-	450	mV
Low Level Output Voltage 2	$V_{OL2}$	3007	I/O Ports P1, P2, P3: $I_{OL} = 1.6mA$ $V_{DD} = 4.5V$ , $V_{SS} = 0V$	-	450	mV
High Level Output Voltage 1	$V_{OH1}$	3006	I/O Port PO, ALE, PSEN: $I_{OH} = -400\mu A$ $V_{DD} = 4.5V$ , $V_{SS} = 0V$	2.4	-	V
High Level Output Voltage 2	$V_{OH2}$	3006	I/O Ports P1, P2, P3: $I_{OH} = -60\mu A$ $V_{DD} = 4.5V$ , $V_{SS} = 0V$	2.4	-	V

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
High Level Output Voltage 3	$V_{OH3}$	3006	I/O Port PO, ALE, PSEN: $I_{OH} = -150\mu A$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 3	3.375	-	V
High Level Output Voltage 4	$V_{OH4}$	3006	I/O Ports P1, P2, P3: $I_{OH} = -25\mu A$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 3	3.375	-	V
High Level Output Voltage 5	$V_{OH5}$	3006	I/O Port PO, ALE, PSEN: $I_{OH} = -40\mu A$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 3	4.05	-	V
High Level Output Voltage 6	$V_{OH6}$	3006	I/O Ports P1, P2, P3: $I_{OH} = -10\mu A$ $V_{DD} = 4.5V, V_{SS} = 0V$ Note 3	4.05	-	V
Idle Supply Current	$I_{DDI}$	3005	$V_{IL} = 0.5V, V_{IH} = 5V$ $V_{IN}(\overline{EA}, RST) = 0V$ $V_{IN}(P0.n) = 5.5V$ XTAL2 = NC All Outputs Open $f = 30MHz$ $V_{DD} = 5.5V, V_{SS} = 0V$ Note 4	-	15	mA
Operating Supply Current	$I_{DDOP}$	3005	$V_{IL} = 0.5V, V_{IH} = 5V$ $V_{IN}(\overline{EA}, RST, P0.n) = 0V$ XTAL2 = NC All Outputs Open $f = 30MHz$ $V_{DD} = 5.5V, V_{SS} = 0V$ Note 4	-	50	mA
Power-Down Supply Current 1	$I_{DDPD1}$	3005	All Outputs Open $V_{IN}(\overline{EA}, P0.n) = 2V$ $V_{IN}(RST, XTAL1) = 0V$ XTAL2 = NC $V_{DD} = 2V, V_{SS} = 0V$ Note 3	-	75	$\mu A$
Power-Down Supply Current 2	$I_{DDPD2}$	3005	All Outputs Open $V_{IN}(\overline{EA}, P0.n) = 5.5V$ $V_{IN}(RST, XTAL1) = 0V$ XTAL2 = NC $V_{DD} = 5.5V, V_{SS} = 0V$	-	75	$\mu A$
Reset Resistor	$R_{RST}$	-	$V_{DD} = 4.5V, V_{SS} = 0V$	50	200	k $\Omega$

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Input Capacitance	$C_{IN}$	3012	$V_{IN}$ (Not Under Test) = 0V $f = 1\text{MHz}$ $V_{DD} = V_{SS} = 0\text{V}$ Note 5	-	10	pF
Output Capacitance	$C_{OUT}$	3012	$V_{OUT}$ (Not Under Test) = 0V $f = 1\text{MHz}$ $V_{DD} = V_{SS} = 0\text{V}$ Note 5	-	10	pF
Address Latch Enable Pulse Width	$t_{LHLL}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	60	-	ns
Address Valid to Address Latch Enable	$t_{AVLL}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	15	-	ns
Address Hold to Address Latch Enable	$t_{LLAX}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	35	-	ns
Address Latch Enable to Valid Instruction In	$t_{LLIV}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	100	-	ns
Programme Store Enable to Valid Instruction In	$t_{PLIV}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	65	-	ns
Address to Valid Instruction In	$t_{AVIV}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	130	-	ns
Programme Store Enable Low to Address Float	$t_{PLAZ}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	-	6	ns
Read Strobe to Valid Data In	$t_{RLDV}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	135	-	ns
Address Latch Enable to Valid Data In	$t_{LLDV}$	3003	$f = 30\text{MHz}$ $V_{DD} = 4.5 \text{ \& } 5.5\text{V}$ $V_{SS} = 0\text{V}$ Note 6	235	-	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Address Latch Enable to Write Strobe	$t_{LLWL}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Note 6	90	115	ns
Address to Write Strobe	$t_{AVWL}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Note 6	115	-	ns
Address to Read Strobe	$t_{AVRL}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Note 6	115	-	ns
Address Latch Enable to Programme Store Enable	$t_{LLPL}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	25	-	ns
Programme Store Enable Pulse Width	$t_{PLPH}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	80	-	ns
Programme Store Enable to Input Instruction Hold	$t_{PXIX}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	-	0	ns
Programme Store Enable to Input Instruction Float	$t_{PXIZ}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	-	30	ns
Programme Store Enable to Address Valid	$t_{PXAV}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	30	-	ns
Read Strobe Pulse Width	$t_{RLRH}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	180	-	ns
Write Strobe Pulse Width	$t_{WLWH}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	180	-	ns
Address Latch Enable to Data Address Hold	$t_{LLAXR}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	55	-	ns
Read Strobe to Data Hold	$t_{RHDX}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	-	0	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Read Strobe to Data Float	$t_{RHDZ}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	60	-	ns
Address to Valid Data In	$t_{AVDV}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	260	-	ns
Address Latch Enable to Read Strobe	$t_{LLRL}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	90	115	ns
Data Valid to Write Strobe	$t_{QVWX}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	20	-	ns
Data Setup to Write Strobe high	$t_{QVWH}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	215	-	ns
Write Strobe to Data Hold	$t_{WHQX}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	20	-	ns
Read Strobe to Address Float	$t_{RLAZ}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	-	0	ns
Write Strobe to Address Latch Enable High	$t_{WHLH}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	20	40	ns
Read Strobe High to Address Latch Enable High	$t_{RHLH}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	20	40	ns
Serial Port Clock Cycle Time	$t_{XLXL}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	400	-	ns
Out Data Setup to Clock	$t_{QVXH}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	300	-	ns
Clock to Out Data Hold	$t_{XHGX}$	3003	f = 30MHz $V_{DD} = 4.5 \text{ \& } 5.5V$ $V_{SS} = 0V$ Notes 3, 6	50	-	ns



Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Clock to In Data Hold	$t_{\text{HDX}}$	3003	f = 30MHz $V_{\text{DD}} = 4.5 \text{ \& } 5.5\text{V}$ $V_{\text{SS}} = 0\text{V}$ Notes 3, 6	-	0	ns
Clock High to In Data Valid	$t_{\text{HDV}}$	3003	f = 30MHz $V_{\text{DD}} = 4.5 \text{ \& } 5.5\text{V}$ $V_{\text{SS}} = 0\text{V}$ Notes 3, 6	300	-	ns

**NOTES:**

1. Unless otherwise specified all inputs and outputs shall be tested for each characteristic, inputs not under test shall be  $V_{\text{IN}} = V_{\text{SS}}$  or  $V_{\text{DD}}$  and outputs not under test shall be open.
2. Functional test shall verify the operation of the instruction set, internal registers, interrupts, timer, serial port, external data, programme counter, RAM, idle mode and the power-down mode.  
Functional test shall also guarantee the following parameters:  
 $V_{\text{IL min}} = -0.5\text{V}$        $V_{\text{IL max}} = 0.2V_{\text{DD}} - 0.25\text{V}$  (0.85V at 5.5V)  
 Except pin  $\overline{\text{EA}}$ :  $V_{\text{IL max}} = 0.2V_{\text{DD}} - 0.45\text{V}$ .  
  
 $V_{\text{IH max}} = V_{\text{DD}} + 0.5\text{V}$      $V_{\text{IH min}} = 0.2V_{\text{DD}} + 1.1\text{V}$  (2V at 4.5V)  
 Except pins XTAL1, RST:  $V_{\text{IH min}} = 0.7V_{\text{DD}} + 0.2\text{V}$ .
3. Guaranteed but not tested.
4. XTAL1 is driven with  $t_{\text{CLCH}} = t_{\text{CHCL}} = 5\text{ns}$ .
5. Characterised at initial design or at major design or process change. Guaranteed but not tested.
6. For AC parameter measurements unless otherwise stated:
  - The load capacitance for I/O Port P0, ALE and  $\overline{\text{PSEN}} = 100\text{pF}$
  - The load capacitance for all other outputs = 80pF
  - Refer to Timing Diagrams herein.

2.3.2 High and Low Temperatures Electrical Measurements

The measurements shall be performed at  $T_{\text{amb}} = +125 (+0 -5)^{\circ}\text{C}$  and  $T_{\text{amb}} = -55 (+5 -0)^{\circ}\text{C}$ .

The characteristics, test methods, conditions and limits shall be the same as specified for Room Temperature Electrical Measurements.

2.4 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at  $T_{amb} = +22 \pm 3^{\circ}C$ .

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values ( $\Delta$ ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value $\Delta$	Absolute		
			Min	Max	
Low Level Input Leakage Current 1	$I_{IL1}$	$\pm 1$	-	$\pm 10$	$\mu A$
Low Level Input Current 2	$I_{IL2}$	$\pm 7.5$	-	-75	$\mu A$
High Level Input Leakage Current	$I_{IH}$	$\pm 1$	-	$\pm 10$	$\mu A$
High Level to Low Level Transition Current	$I_{IT}$	$\pm 75$	-	-750	$\mu A$
Low Level Output Voltage 1	$V_{OL1}$	$\pm 40$	-	450	mV
Low Level Output Voltage 2	$V_{OL2}$	$\pm 40$	-	450	mV
High Level Output Voltage 1	$V_{OH1}$	$\pm 0.2$	2.4	-	V
High Level Output Voltage 2	$V_{OH2}$	$\pm 0.2$	2.4	-	V
Operating Supply Current	$I_{DDOP}$	$\pm 5$	-	50	mA
Power-Down Supply Current 2	$I_{DDPD2}$	$\pm 7.5$	-	75	$\mu A$

2.5 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at  $T_{amb} = +22 \pm 3^{\circ}C$ .

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values ( $\Delta$ ) shall not be exceeded for each characteristic where specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Functional Test 1	-	-	-	-
Functional Test 2	-	-	-	-
Functional Test 3	-	-	-	-
Functional Test 4	-	-	-	-
Functional Test 5	-	-	-	-

Characteristics	Symbols	Limits		Units
		Min	Max	
Functional Test 6	-	-	-	-
Functional Test 7	-	-	-	-
Functional Test 8	-	-	-	-
Low Level Input Leakage Current 1	$I_{IL1}$	-	$\pm 10$	$\mu A$
Low Level Input Leakage Current 2	$I_{IL2}$	-	-75	$\mu A$
High Level Input Leakage Current	$I_{IH}$	-	$\pm 10$	$\mu A$
High Level to Low Level Transition Current	$I_{IT}$	-	-750	$\mu A$
Low Level Output Voltage 1	$V_{OL1}$	-	450	mV
Low Level Output Voltage 2	$V_{OL2}$	-	450	mV
High Level Output Voltage 1	$V_{OH1}$	2.4	-	V
High Level Output Voltage 2	$V_{OH2}$	2.4	-	V
Idle Supply Current	$I_{DDI}$	-	15	mA
Operating Supply Current	$I_{DDOP}$	-	50	mA
Power-Down Supply Current 2	$I_{DDPD2}$	-	75	mA
Reset Resistor	$R_{RST}$	50	200	k $\Omega$
Address Latch Enable Pulse Width	$t_{LHLL}$	60	-	ns
Address Valid to Address Latch Enable	$t_{AVLL}$	15	-	ns
Address Hold to Address Latch Enable	$t_{LLAX}$	35	-	ns
Address Latch Enable to Valid Instruction In	$t_{LLIV}$	100	-	ns
Programme Store Enable to Valid Instruction In	$t_{PLIV}$	65	-	ns
Address to Valid Instruction In	$t_{AVIV}$	130	-	ns
Read Strobe to Valid Data In	$t_{RLDV}$	135	-	ns
Address Latch Enable to Valid Data In	$t_{LLDV}$	235	-	ns
Address Latch Enable to Write Strobe	$t_{LLWL}$	90	115	ns
Address to Write Strobe	$t_{AVWL}$	115	-	ns
Address to Read Strobe	$t_{AVRL}$	115	-	ns

2.6 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	$T_{amb}$	+125 (+0 -5)	°C
Outputs P0.n, P1.n, P2.n, P3.n, PSEN, ALE	$V_{OUT}$	Parallel Connected (Notes 1, 2)	V
Input $\overline{EA}$	$V_{IN}$	$V_{DD}$ (Notes 1, 2)	V
Output XTAL2	$V_{OUT}$	$V_{SS}$ (Notes 1, 2)	V
Input XTAL1	$V_{IN}$	$V_{GEN1}$ (Notes 1, 2)	V
Input RST	$V_{IN}$	$V_{GEN2}$ (Notes 1, 2)	V
Pulse Voltage	$V_{GEN}$	0V to $V_{DD}$	V
Pulse Frequency Square Wave	$f_{GEN1}$	400k $\pm$ 20% 50% Duty Cycle	Hz
Pulse Frequency Square Wave	$f_{GEN2}$	3.77k 22.6% Duty Cycle	Hz
Positive Supply Voltage	$V_{DD}$	+5.5 (+0 -0.5)	V
Negative Supply Voltage	$V_{SS}$	0	V

**NOTES:**

1. Input Protection Resistor = Output Load = 1k $\Omega$ .
2. All inputs and outputs are connected to their equivalents on each device by a common bus.

2.7 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

2.8 TOTAL DOSE RADIATION TESTING

2.8.1 Bias Conditions and Total Dose Level for Total Dose Radiation Testing

Continuous bias shall be applied during radiation testing as specified below.

The total dose level applied shall be as specified in the component type variant information herein or in the Purchase Order.

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T <sub>amb</sub>	+22 ±3	°C
Output XTAL2	V <sub>OUT</sub>	Open	V
Input RST	V <sub>IN</sub>	V <sub>GEN</sub> (Note 1)	V
Inputs/Outputs Remaining	V <sub>IN/OUT</sub>	V <sub>DD</sub> (Note 1)	V
Pulse Voltage	V <sub>GEN</sub>	0 to V <sub>DD</sub>	V
Pulse Frequency Square Wave	f <sub>GEN</sub>	3.77k 22.6% Duty Cycle	Hz
Positive Supply Voltage	V <sub>DD</sub>	5 ±0.1	V
Negative Supply Voltage	V <sub>SS</sub>	0	V

**NOTES:**

1. Input Protection Resistor = Output Load = 1kΩ.

2.8.2 Electrical Measurements for Total Dose Radiation Testing

Prior to radiation testing the devices shall successfully meet Room Temperature Electrical Measurements specified herein.

Unless otherwise stated the measurements shall be performed at T<sub>amb</sub> = +22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in electrical measurements at Room Temperature.

The parameters to be measured during and on completion of radiation testing are shown below.

Unless otherwise specified all inputs and outputs shall be tested for each characteristic.

Characteristics	Symbols	Limits		Units
		Min	Max	
Idle Supply Current	I <sub>IL1</sub>	-	±10	µA
High Level Input Leakage Current 1	I <sub>IH</sub>	-	±10	µA
Low Level Input Leakage Current 2	I <sub>IL2</sub>	-	-75	µA
High Level to Low Level Transition Current	I <sub>IT</sub>	-	-750	µA
Low Level Output Voltage 1	V <sub>OL1</sub>	-	450	mV

Characteristics	Symbols	Limits		Units
		Min	Max	
Low Level Output Voltage 2	$V_{OL2}$	-	450	mV
High Level Output Voltage 1	$V_{OH1}$	2.4	-	V
High Level Output Voltage 2	$V_{OH2}$	2.4	-	V
Idle Supply Current	$I_{DDI}$	-	100	mA
Operating Supply Current	$I_{DDOP}$	-	100	mA
Power-Down Supply Current 2	$I_{DDPD2}$	-	15	mA